# MMPN080x Series



### **PIN Diodes**

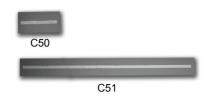
Rev. V2

### **Features**

- · High Isolation
- Broadband Performance up to 50 GHz

## **Description**

The MMPN series are distributed PIN diodes that are integrated into a 50  $\Omega$  microstrip transmission line. These PIN diodes are designed to be operated as shunt, reflective attenuators.



# Electrical Specifications: $T_A = +25$ °C

Model	Frequency (GHz)	Maximum Reversed Current (nA)	Minimum Breakdown Voltage (V)	Maximum Insertion Loss (dB)	Minimum Return Loss (dB)	Minimum Isolation (dB)	Outline
MMPN080045	2 - 20	100	200	1	12	30	C50
MMPN080150	2 - 35	200	200	3	12	50	C51
Test Conditions		V <sub>R</sub> = 30 V	I <sub>R</sub> = 10 μA	V <sub>R</sub> = 0 V	$V_R = 0 V$	I <sub>F</sub> = 40 mA	

## **Absolute Maximum Ratings**

Parameter	Absolute Maximum		
Reverse Voltage	200 V		
Forward Current	150 mA		
Thermal Resistance	60°CW		
Junction Temperature	+175°C		
Storage Temperature	-65°C to +200°C		
Mounting / Bonding Temperature	+320°C for 10 seconds		

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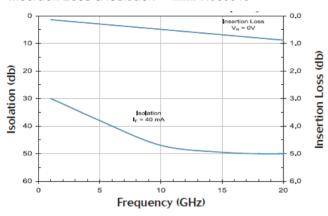


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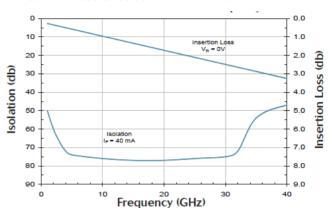
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# Typical RF Performance Curves @ +25°C

#### Insertion Loss & Isolation - MMPN080045



#### Insertion Loss & Isolation - MMPN080150



# **Outline Drawings**

